



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 30V
- I_D 3.6A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 33mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 48mohm
- 100% V_{DS} Tested

General Description

- Trench Power MV MOSFET technology
- High Power and current handing capability
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- PWM application
- Load switch

■ Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
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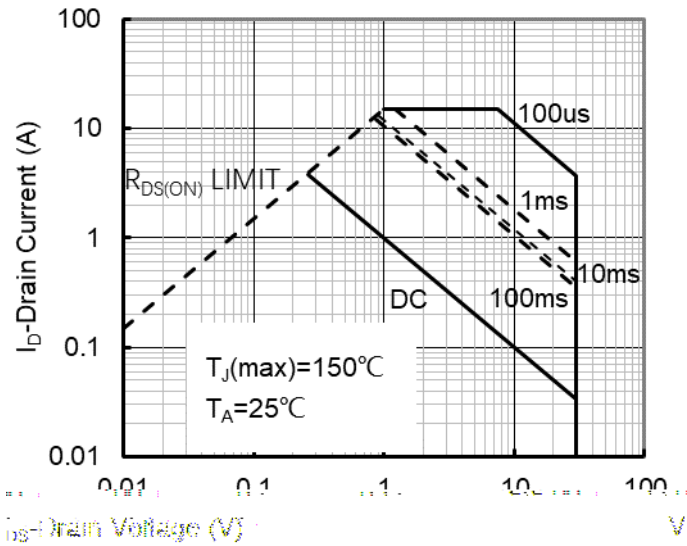


Figure7. Safe Operation Area

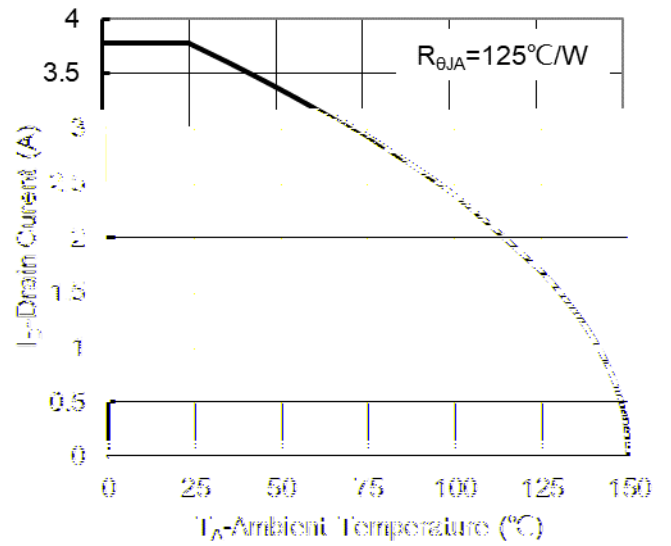


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

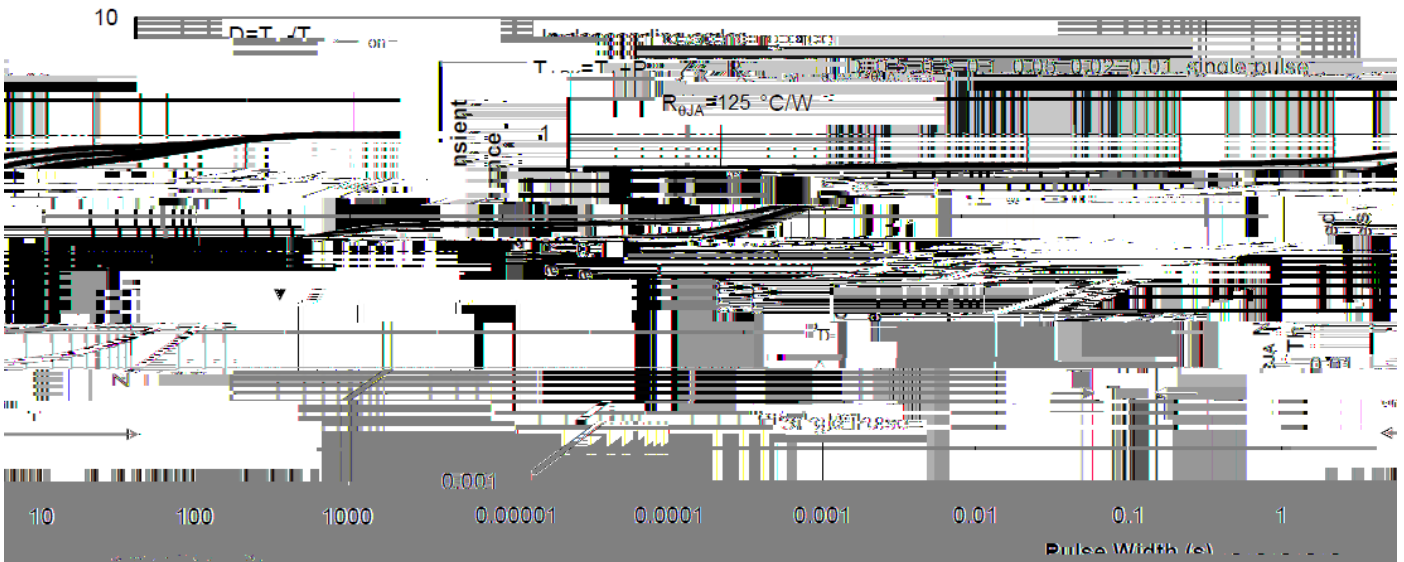
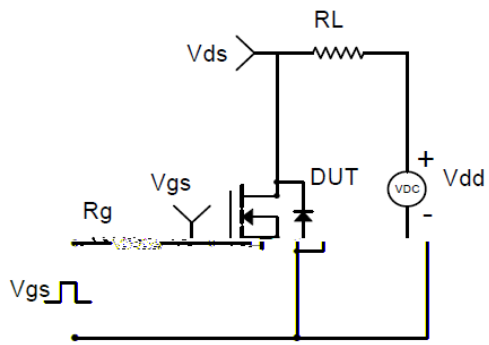
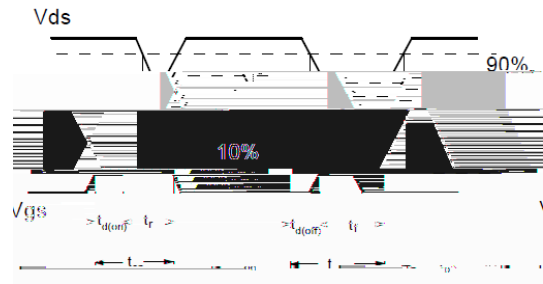


Figure9. Normalized Maximum Transient Thermal Impedance

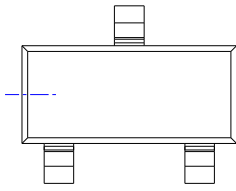


Resistive





■ SOT-23 Package information



UNIT mm



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